

Product data sheet

1. General description

NPN low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a leadless ultra small DFN1010D-3 (SOT1215) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

PNP complement: PBSS5230QA.

2. Features and benefits

- Very low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain h_{FE} at high I_C
- High energy efficiency due to less heat generation
- Reduced Printed-Circuit Board (PCB) area requirements
- Solderable side pads
- AEC-Q101 qualified

3. Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

4. Quick reference data

Table 1. Quick reference data							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base		-	-	30	V
I _C	collector current			-	-	2	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	3	А
R _{CEsat}	collector-emitter saturation resistance	$\begin{split} I_C &= 1 \text{ A}; I_B = 100 \text{ mA}; \text{ pulsed}; \\ t_p &\leq 300 \mu\text{s}; \delta \leq 0.02 ; T_{amb} = 25 ^\circ\text{C} \end{split}$		-	135	180	mΩ

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		С
2	E	emitter		в
3	С	collector	4 3	- N
4	С	collector		E sym123
			Transparent top view DFN1010D-3 (SOT1215)	

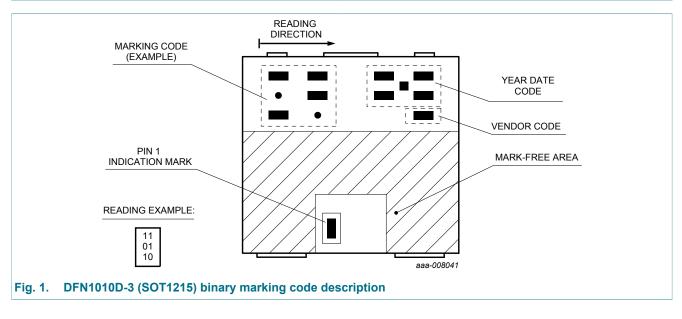
6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
PBSS4230QA	DFN1010D-3	plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals	SOT1215			

7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS4230QA	01 11 00



PBSS4230QA

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V _{CBO}	collector-base voltage	open emitter		-	30	V
V _{CEO}	collector-emitter voltage	open base		-	30	V
V _{EBO}	emitter-base voltage	open collector		-	7	V
I _C	collector current			-	2	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	3	А
I _B	base current			-	0.3	А
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	1	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	325	mW
			[2]	-	600	mW
			[3]	-	740	mW
			[4]	-	540	mW
			[5]	-	1000	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 PCB single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 1 cm².

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm².

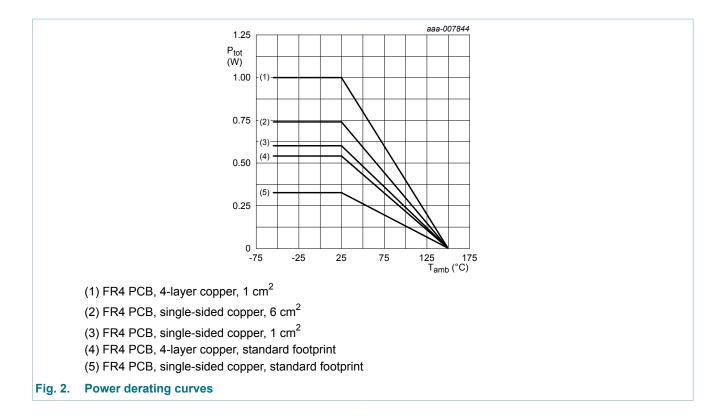
[4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

^[5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated mounting pad for collector 1 cm².

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9. Thermal characteristics

Table 6. T	hermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from junction to ambient		in free air	[1]	-	-	385	K/W
		[2]	-	-	209	K/W	
	ampient		[3]	-	-	169	K/W
			[4]	-	-	232	K/W
	[5]		-	-	125	K/W	

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 1 cm².

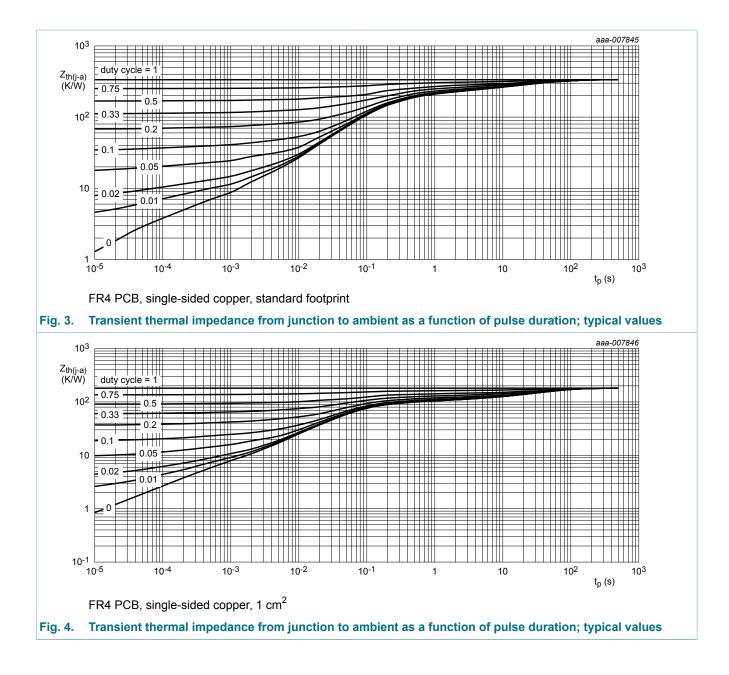
[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm².

[4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

^[5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated mounting pad for collector 1 cm².

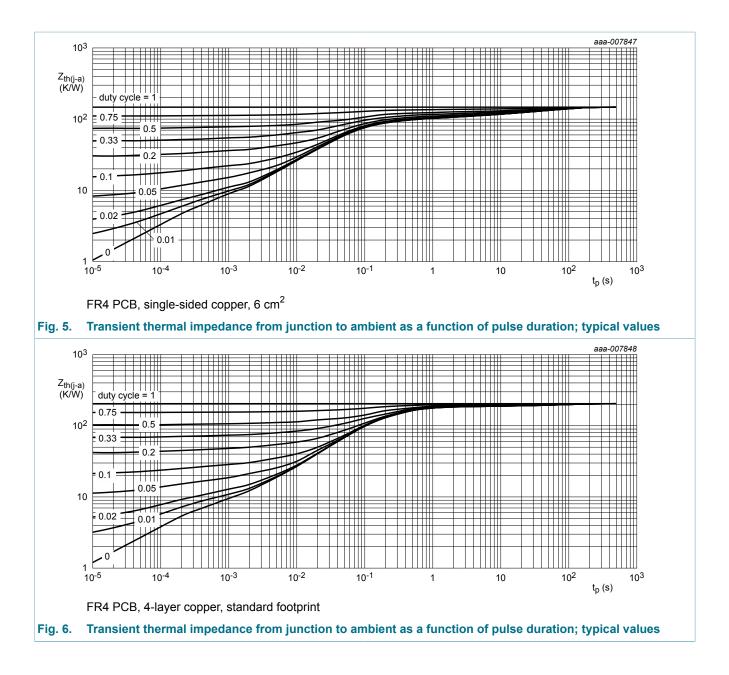


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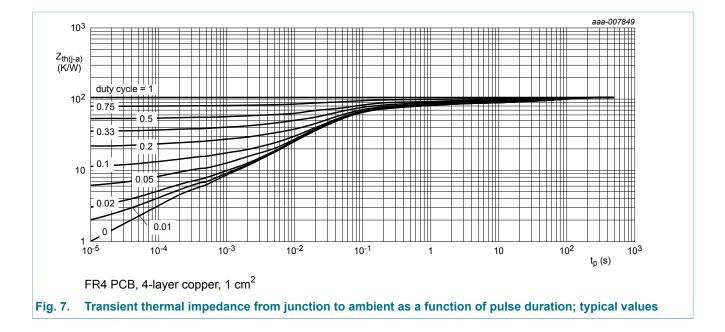
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10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 24 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 24 V; I _E = 0 A; T _j = 150 °C	-	-	50	μA
I _{CES}	collector-emitter cut-off current	V_{CE} = 24 V; V_{BE} = 0 V; T_{amb} = 25 °C	-	-	100	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V_{CE} = 2 V; I _C = 100 mA; pulsed; t _p ≤ 300 µs; \overline{o} ≤ 0.02 ; T _{amb} = 25 °C	250	430	-	
		$\begin{split} V_{CE} &= 2 \text{ V; } I_C = 500 \text{ mA; pulsed;} \\ t_p &\leq 300 \mu\text{s; } \delta \leq 0.02 \text{ ; } T_{amb} = 25 ^\circ\text{C} \end{split}$	230	380	-	
		$\label{eq:Vce} \begin{split} V_{CE} &= 2 \; V; \; I_C = 1 \; A; \; \text{pulsed}; \; t_p \leq 300 \; \mu s; \\ \delta &\leq 0.02 \; ; \; T_{amb} = 25 \; ^\circ \text{C} \end{split}$	180	290	-	
		$\label{eq:Vce} \begin{split} V_{CE} &= 2 \; \text{V; I}_{C} = 2 \; \text{A; pulsed; } t_{p} \leq 300 \; \mu\text{s;} \\ \delta \leq 0.02 \; \text{; } T_{amb} = 25 \; ^{\circ}\text{C} \end{split}$	100	160	-	
V _{CEsat}	collector-emitter saturation voltage	I _C = 500 mA; I _B = 50 mA; pulsed; t _p ≤ 300 μs; \overline{o} ≤ 0.02 ; T _{amb} = 25 °C	-	75	100	mV
		I_{C} = 1 A; I_{B} = 50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	140	190	mV
		I_{C} = 1 A; I_{B} = 100 mA; pulsed; $t_{p} \le 300 \ \mu$ s; $\bar{o} \le 0.02$; T_{amb} = 25 °C	-	135	180	mV

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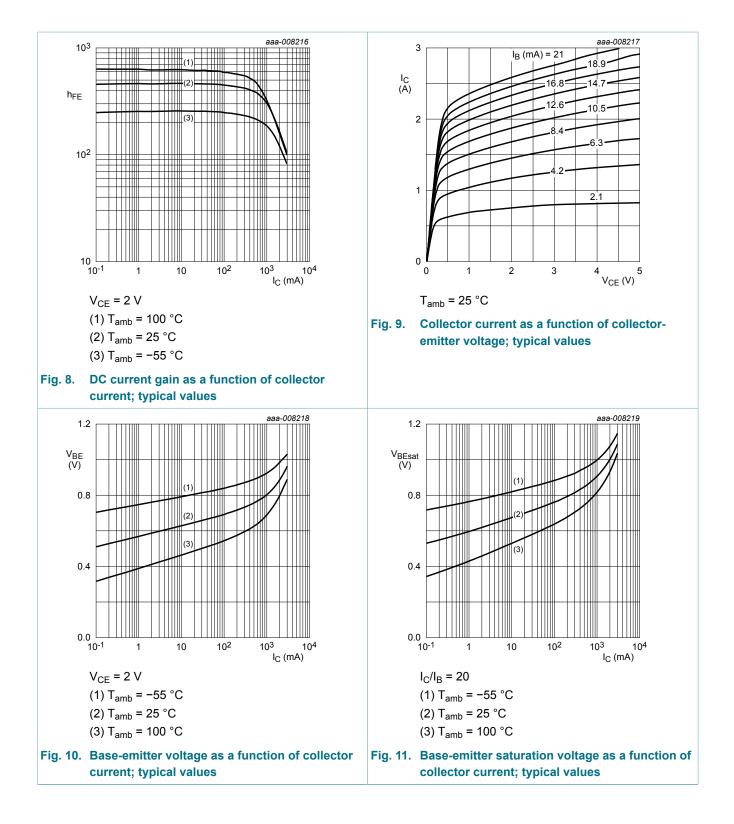
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Symbol	Parameter	Conditions	M	n Typ	Мах	Unit
		I_{C} = 2 A; I_{B} = 100 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	265	360	mV
		I_C = 2 A; I_B = 200 mA; pulsed; $t_p \le 300$ μs; δ ≤ 0.02 ; T_{amb} = 25 °C	-	255	350	mV
R _{CEsat}	collector-emitter saturation resistance	I_{C} = 1 A; I_{B} = 100 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	135	180	mΩ
V _{BEsat}	base-emitter saturation voltage	I _C = 500 mA; I _B = 50 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02 ; T _{amb} = 25 °C	-	0.86	1	V
		I_{C} = 1 A; I_{B} = 50 mA; pulsed; $t_{p} \le 300 \ \mu$ s; δ ≤ 0.02 ; T_{amb} = 25 °C	-	0.9	1.05	V
		I_C = 2 A; I_B = 100 mA; pulsed; $t_p \le 300$ μs; δ ≤ 0.02 ; T_{amb} = 25 °C	-	1	1.15	V
		I_C = 2 A; I_B = 200 mA; pulsed; $t_p \le 300$ μs; δ ≤ 0.02 ; T_{amb} = 25 °C	-	1.05	1.2	V
V _{BEon}	base-emitter turn-on voltage	V_{CE} = 2 V; I _C = 0.5 A; pulsed; t _p ≤ 300 µs; δ ≤ 0.02 ; T _{amb} = 25 °C	-	0.75	0.9	V
t _d	delay time	V_{CC} = 10 V; I _C = 0.5 A; I _{Bon} = 25 mA;	-	15	-	ns
t _r	rise time	I _{Boff} = -25 mA; T _{amb} = 25 °C	-	30	-	ns
t _{on}	turn-on time		-	45	-	ns
t _s	storage time		-	425	-	ns
t _f	fall time		-	65	-	ns
t _{off}	turn-off time		-	490	-	ns
f _T	transition frequency	V_{CE} = 10 V; I _C = 50 mA; f = 100 MHz; T _{amb} = 25 °C	1:	30 190	-	MHz
C _c	collector capacitance	V _{CB} = 10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	8	10	pF

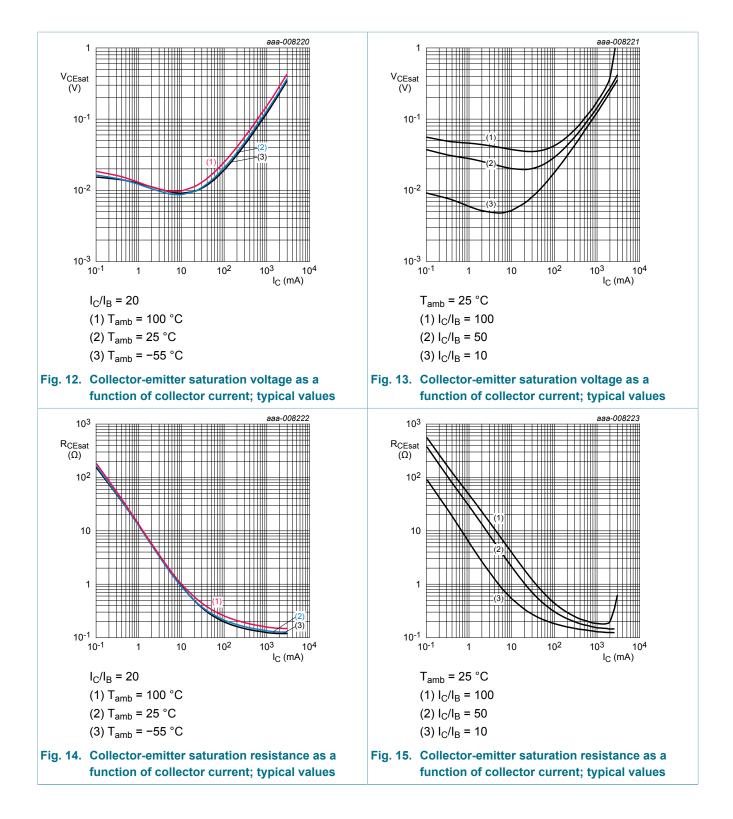
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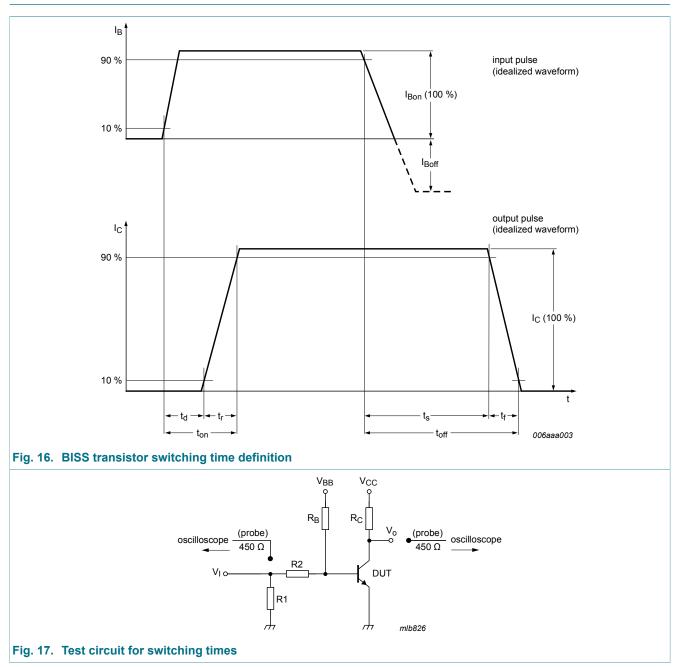
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11. Test information

11.1 Quality information

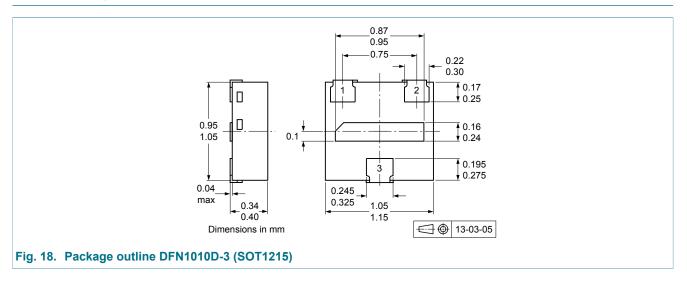
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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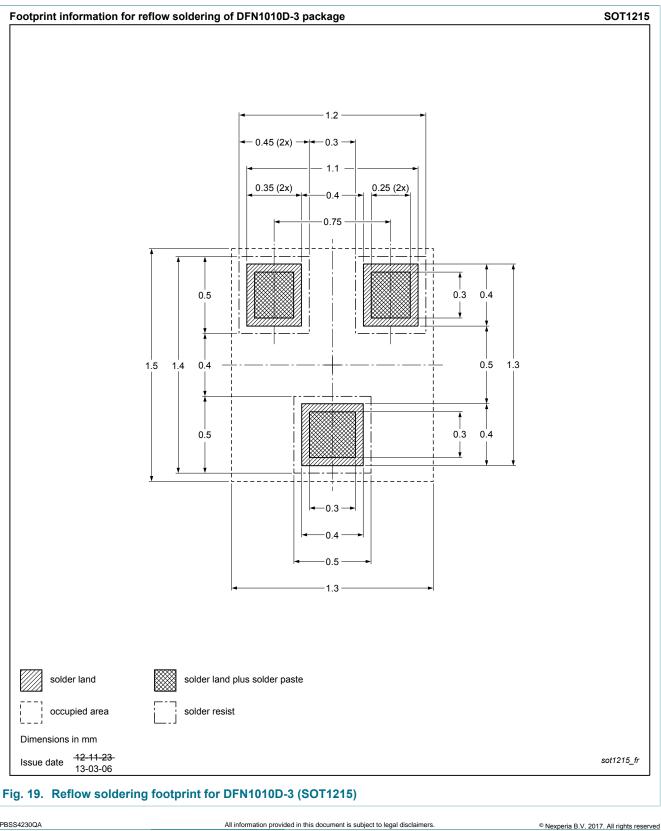
12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history					
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes	
PBSS4230QA v.1	20130823	Product data sheet	-	-	

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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